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(54) MEMORY CIRCUIT, DYNAMIC RANDOM ACCESS MEMORY AND OPERATION METHOD THEREOF

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(57) ABSTRACT

The present disclosure provides a dynamic random access memory, which includes a storage diode and a control-FET. The storage diode is composed of a gate-floating FET, and two source/drains of the gate-floating FET serve as a cathode and an anode of the storage diode. The control FET is electrically connected to the cathode or the anode of the storage diode.

